



Features

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHs compliant

Benefits

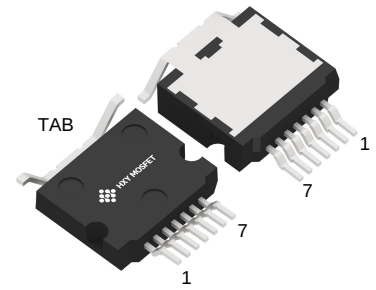
- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink requirements

Applications

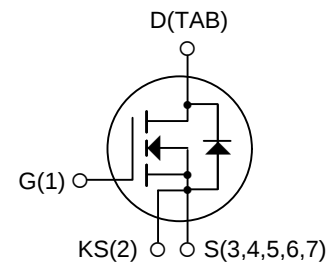
- Switch mode power supplies
- Renewable energy
- On Board Charger
- High Voltage DC/DC Converters



Ordering Part Number	Package	Brand
NTT2023N065M3S	T2PAK	HXY MOSFET



T2PAK



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
V_{DSmax}	Drain-Source Voltage	$V_{GS} = 0V, I_D = 100\mu A$	650	V	
V_{GS}	Gate-Source voltage (transient)	$t_p \leq 500ns, \text{duty cycle} \leq 1\%$	-8/+20	V	
V_{GSop}	Recommend Gate-Source Voltage	Static	-4/+18	V	
I_D	Continuous Drain current	$V_{GS} = 18V, T_c = 25^\circ\text{C}$	84	A	Fig. 14
		$V_{GS} = 18V, T_c = 100^\circ\text{C}$	59		
$I_{D,pulse}$	Pulsed Drain Current	Pulse with t_p limited by T_{jmax}	151	A	
P_D	Power Dissipation	$T_c = 25^\circ\text{C}, T_j = 175^\circ\text{C}$	238	W	Fig.16
T_j	Operating junction temperature		-55~175	$^\circ\text{C}$	
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$	
	TO-247 miunting torque	M3 Screw	0.7	Nm	



Thermal Characteristics

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		0.63		K/W	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		K/W	

Electrical Characteristics (T_c = 25°C unless other wise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	$V_{GS} = 0V, I_D = 100\mu A$	650			V	
$V_{GS(th)}$	Gate Threshold voltage	$V_{GS} = V_{DS}, I_D = 16mA$		3.0		V	Fig. 9
		$V_{GS} = V_{DS}, I_D = 16mA, T_j = 175^\circ C$		2.0			
I_{GSS}	Gate-Source Leakage current	$V_{GS} = 18V, V_{DS} = 0V$			250	nA	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V, T_j = 25^\circ C$		1	50	μA	
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = 18V, I_D = 40A$		26	38	m Ω	Fig. 3, 4, 5
		$V_{GS} = 18V, I_D = 40A, T_j = 175^\circ C$		35			
g_{fs}	Transconductance	$V_{DS} = 18V, I_D = 40A$		27		S	Fig. 6
		$V_{DS} = 18V, I_D = 40A, T_j = 175^\circ C$		25			



Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Q_{GS}	Gate to Source Charge	$V_{DS} = 400V$ $I_D = 40A$ $V_{GS} = -4V/18V$		29		nC	Fig. 10
Q_{GD}	Gate to Drain Charge			35			
Q_G	Total Gate Charge			74.5			

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 600V$ $f = 1\text{ MHz}$ $V_{AC} = 25mV$		2543		pF	Fig. 13
C_{oss}	Output Capacitance			173		pF	
C_{rss}	Reverse Transfer Capacitance			8		pF	
$R_{G(int)}$	Internal Gate Resistance	$f = 1\text{ MHz}, V_{AC} = 25mV$		1.2		Ω	



Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
V_{SD}	Diode Forward Voltage	$V_{GS} = -4V, I_{SD} = 20A$		4.3		V	Fig. 7,8
		$V_{GS} = -4V, I_{SD} = 20A, T_J = 175^{\circ}C$		3.7			
I_S	Continuous Diode Forward Current	$V_{GS} = -4V, T_C = 25^{\circ}C$		51		A	
$I_{S, pulse}$	Diode pulse Current	$V_{GS} = -4V$, pulse width t_p limited by T_{jmax}		151		A	
t_{rr}	Reverse Recovery Time	$V_{GS} = -4V, I_{SD} = 40A, V_R = 400V$ $diff/dt = 3700A/us$		14		nS	
Q_{rr}	Reverse Recovery Charge			221		nC	
I_{rm}	Peak Reverse Recovery Current			24		A	

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 400V, V_{GS} = -4/+18V$ $I_D = 40A, R_{G(ext)} = 5\Omega$ $L = 200\mu H$		1		nS	Fig.21
t_r	Rise Time			21		nS	
$t_{d(off)}$	Turn-Off Delay Time			20		nS	
t_f	Fall Time			5		nS	
E_{on}	Turn-On Energy			88		μJ	Fig.19
E_{off}	Turn-Off Energy			72		μJ	
E_{tot}	Total switching energy			160		μJ	



Typical Performance

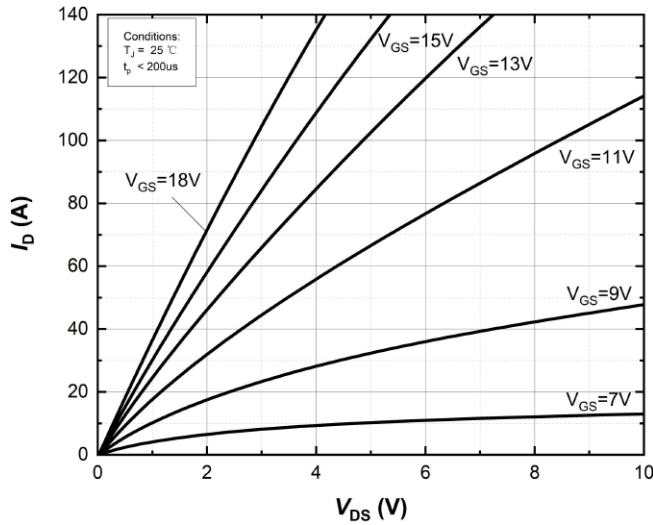


Figure 1. Output characteristics at $T_j=25^\circ\text{C}$

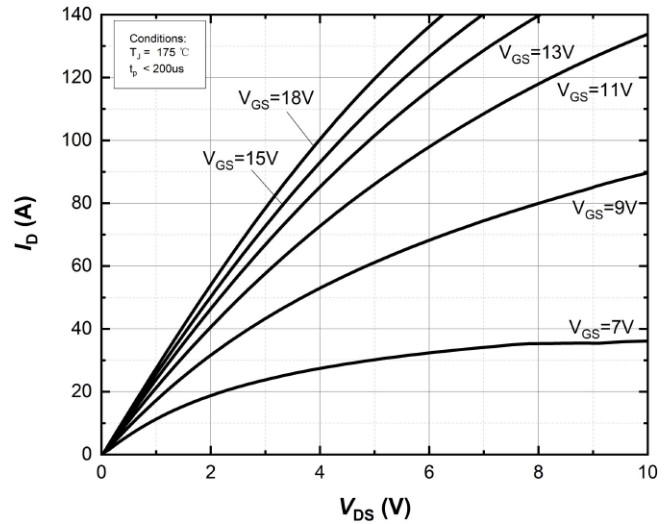


Figure 2. Output characteristics at $T_j=175^\circ\text{C}$

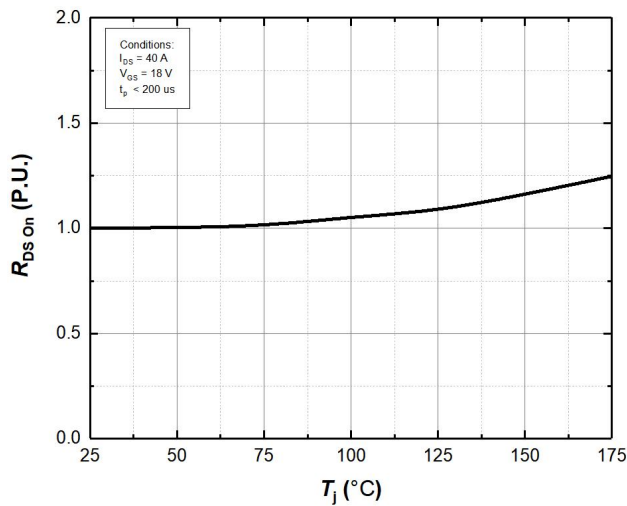


Figure 3. Normalized On-Resistance vs. Temperature

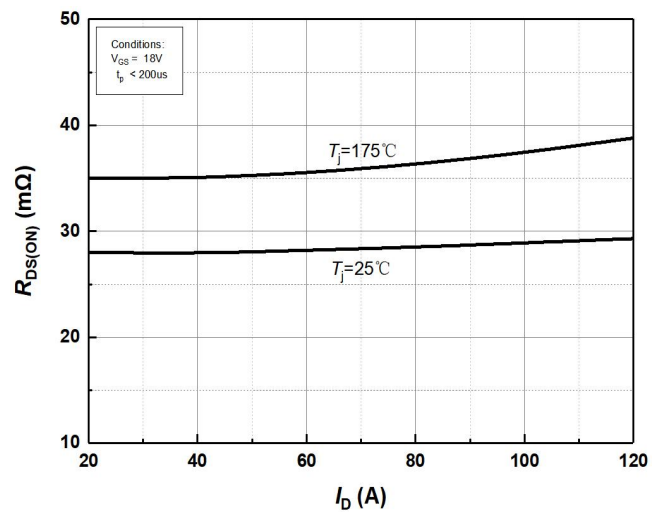


Figure 4. On-Resistance vs. Drain current for Various Temperature

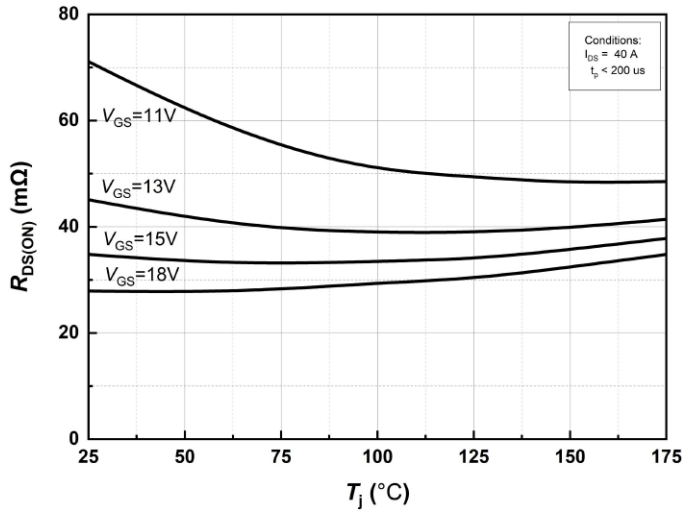


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

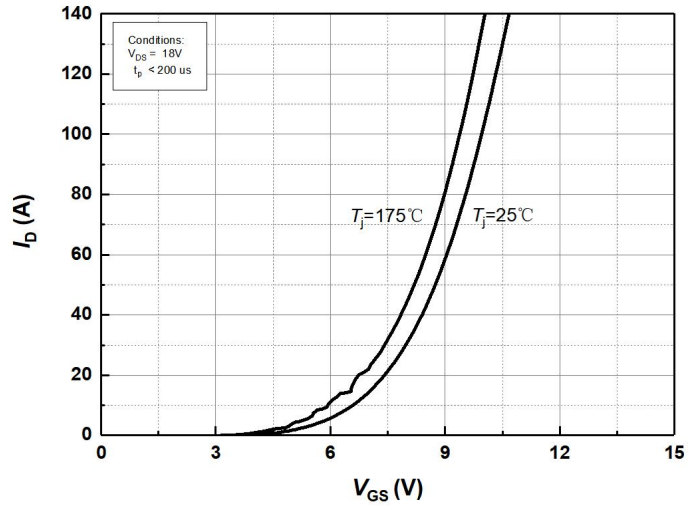


Figure 6. Transfer Characteristics for Various Junction Temperatures

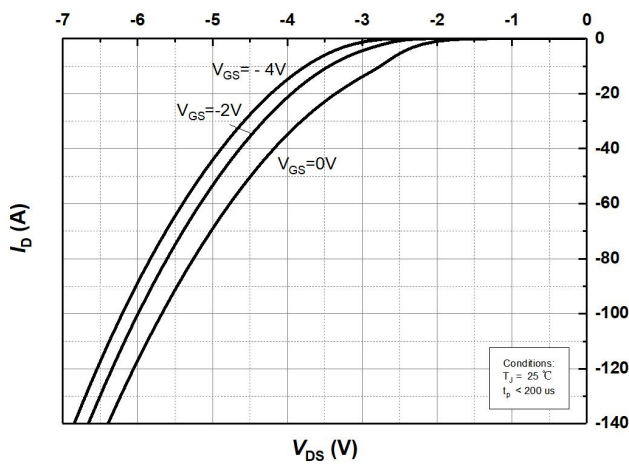


Figure 7. Body Diode Characteristics at $T_j=25^{\circ}\text{C}$

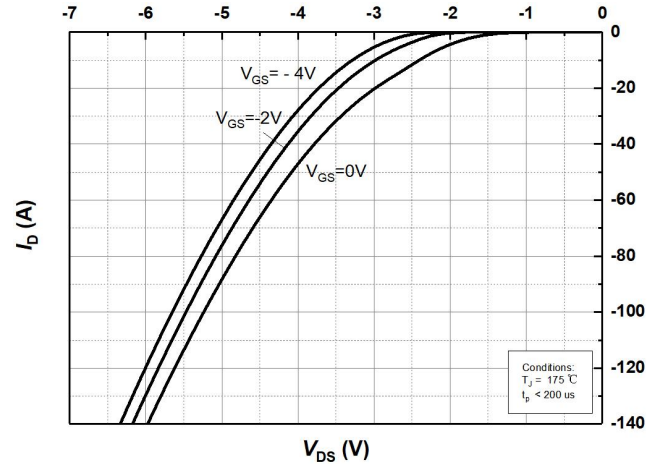


Figure 8. Body Diode Characteristics at $T_j=175^{\circ}\text{C}$

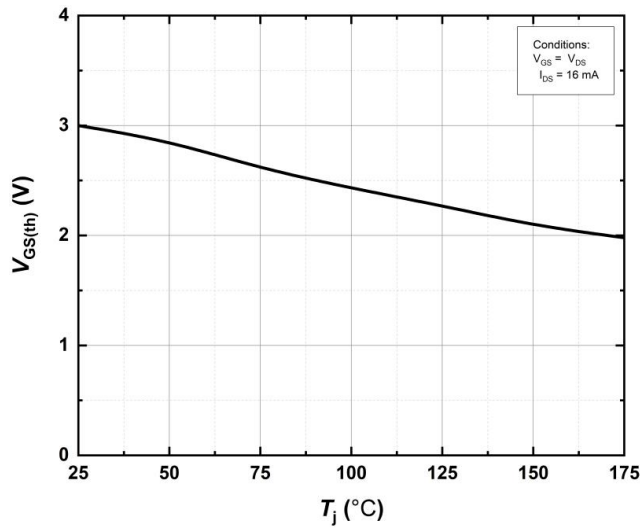


Figure 9. Threshold Voltage vs. Temperature

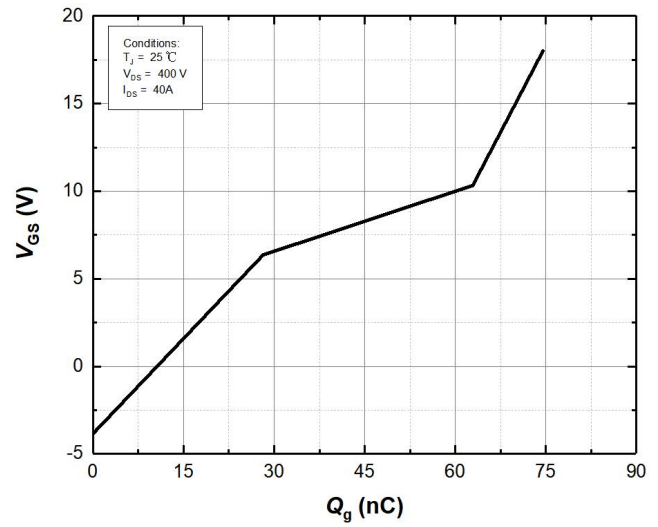


Figure 10 Gate Charge Characteristics

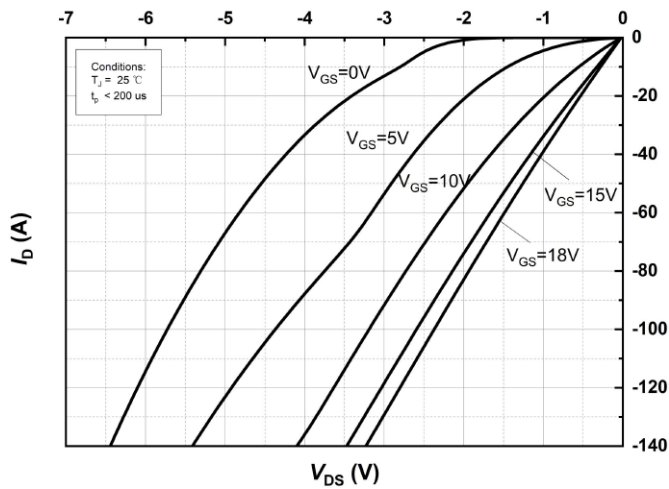


Figure 11. 3rd Quadrant Characteristic at $T_J=25^{\circ}\text{C}$

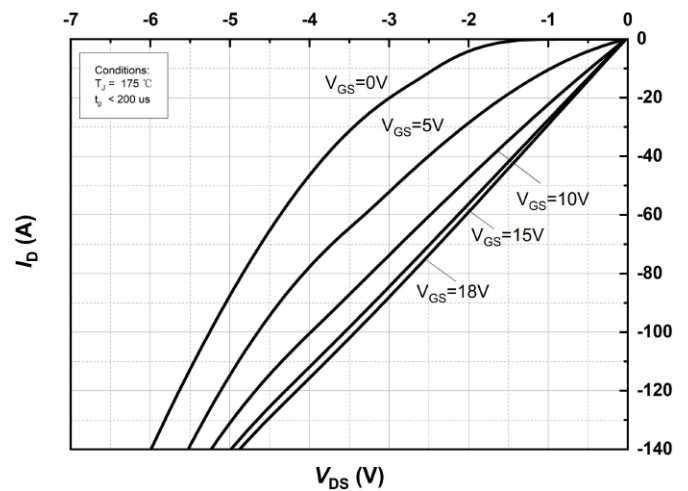


Figure 12. 3rd Quadrant Characteristic at $T_J=175^{\circ}\text{C}$

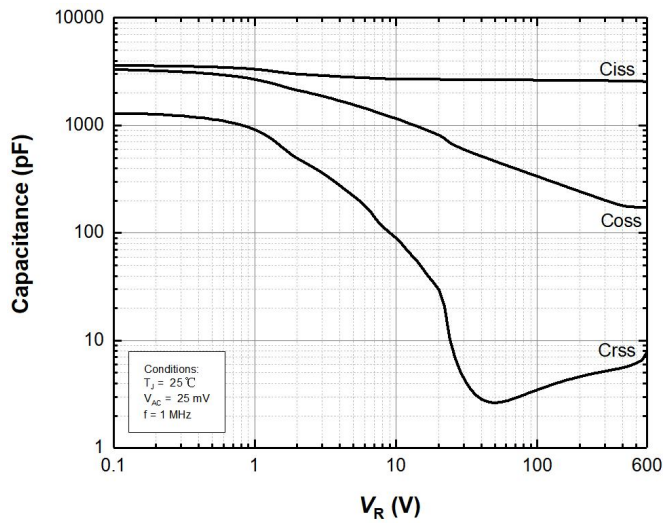


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

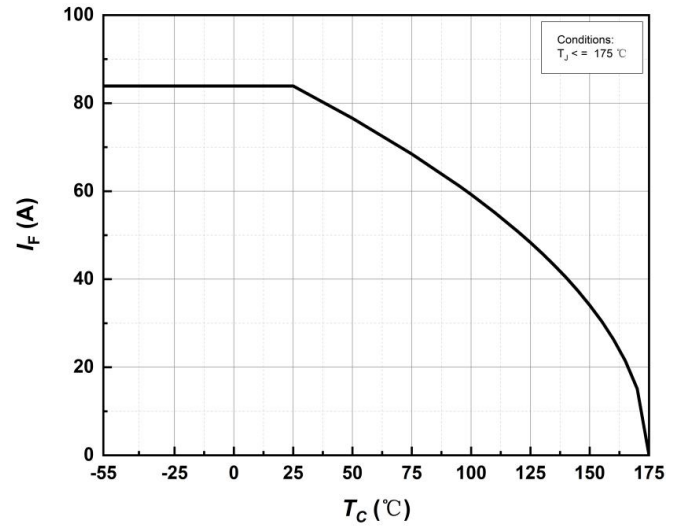


Figure 14. Continuous Drain Current Derating vs Case Temperature

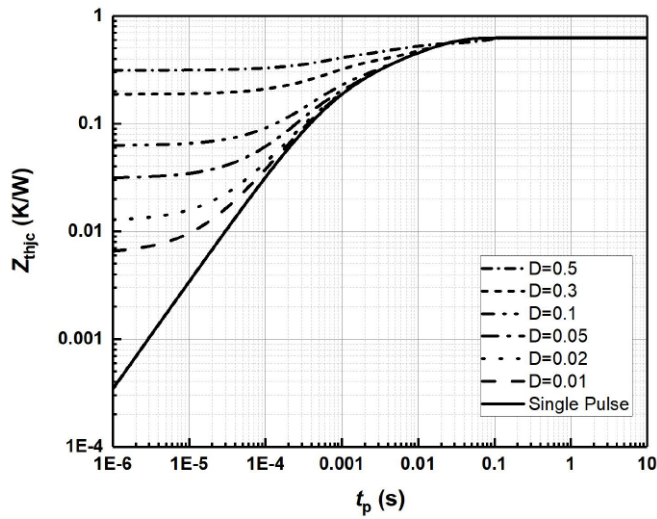


Figure 15. Transient Thermal Impedance (Junction – Case)

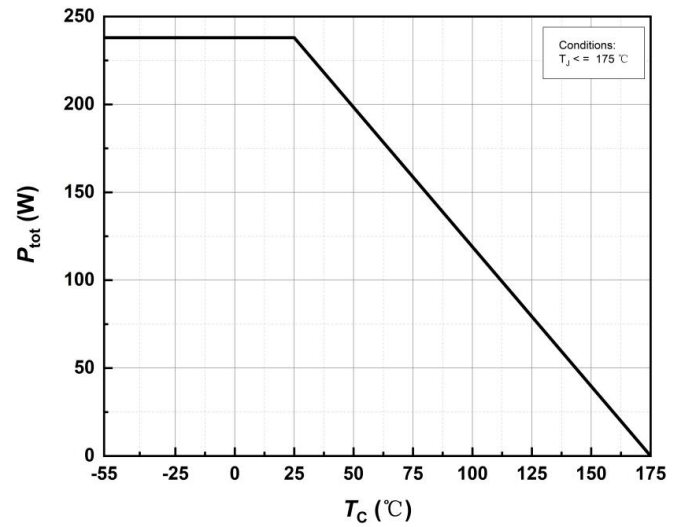


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

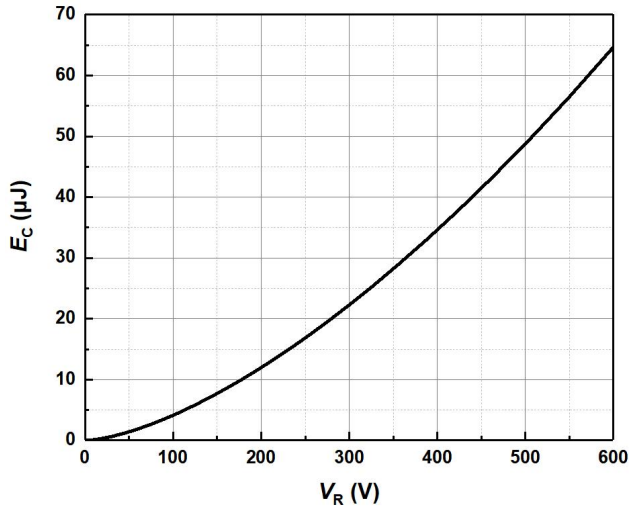


Figure 17. Output Capacitor Stored Energy

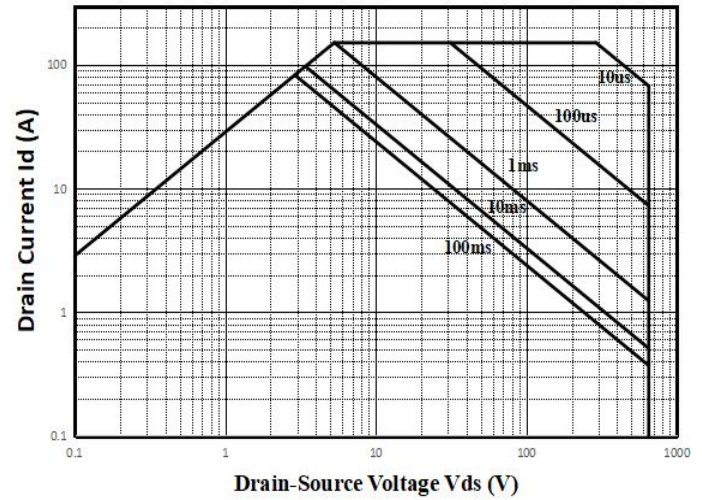


Figure 18. Safe Operating Area

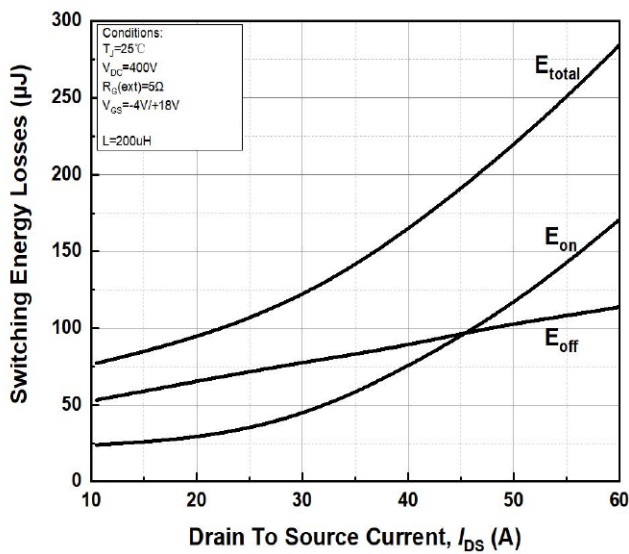


Figure 19. Clamped Inductive Switching Energy vs. Drain Current($V_{DD} = 400V$)

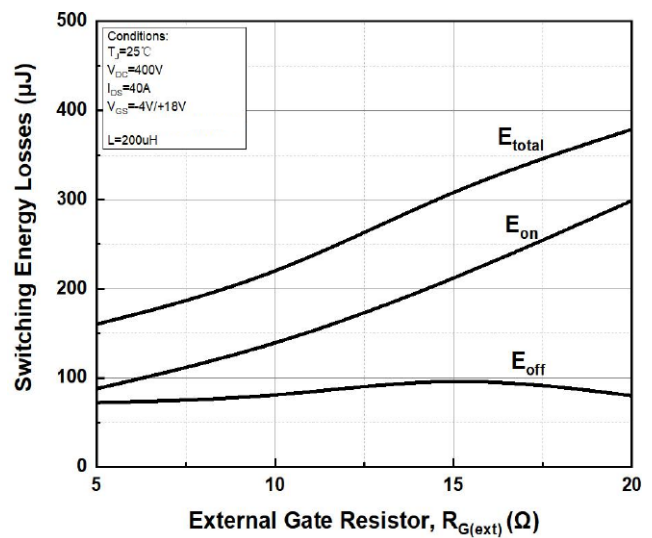


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

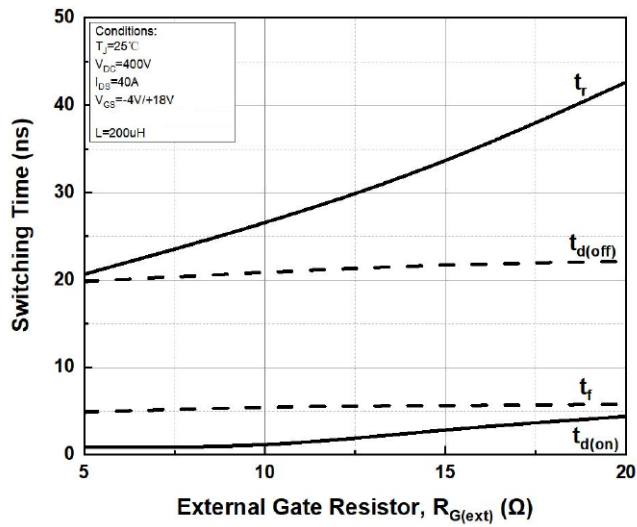
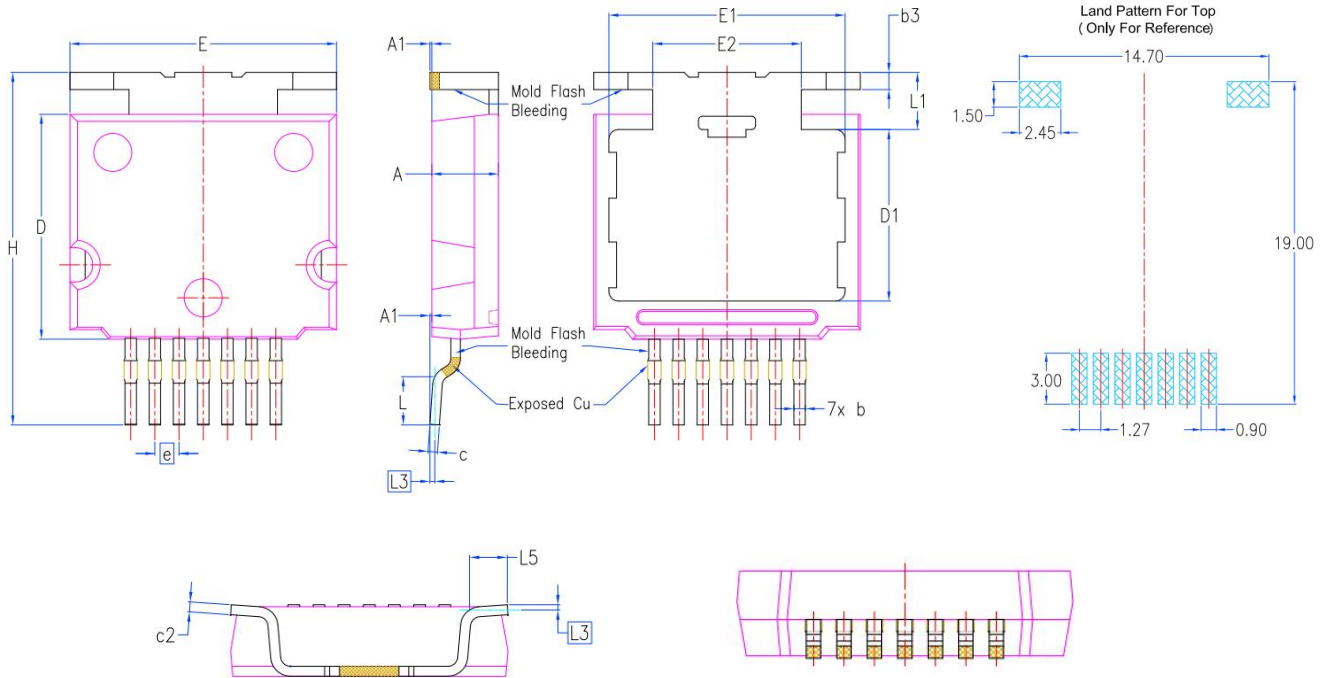


Figure 21. Switching Times vs. $R_{G(\text{ext})}$



Package Dimensions

Package T2PAK



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	3.40	3.50	3.60
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
b3	0.80	0.90	1.00
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D	11.70	11.80	11.90
D1	8.80	9.00	9.10
E	13.90	14.00	14.10
E1	12.30	12.40	12.50
E2	7.75	7.80	7.85
e	1.27 BSC		
H	18.00	18.50	19.00
L	2.30	2.50	2.75
L1	---	3.05	---
L3	---	0.26	---
L5	1.70	1.90	2.15



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